

## Silicon NPN Power Transistors

2SD2333

## DESCRIPTION

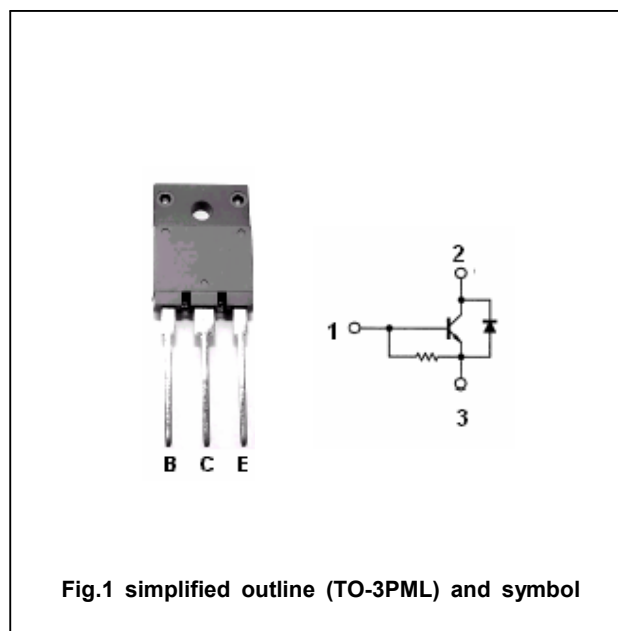
- With TO-3PML package
- High breakdown voltage
- Built-in damper diode

## APPLICATIONS

www.DataSheet4U.com Color TV horizontal deflection output applications

## PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter

Absolute maximum ratings( $T_a=25^\circ\text{C}$ )

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$V_{CBO}$	Collector-base voltage	Open emitter	1500	V
$V_{CEO}$	Collector-emitter voltage	Open base	600	V
$V_{EBO}$	Emitter-base voltage	Open collector	5	V
$I_C$	Collector current		5	A
$I_{BM}$	Base current-peak		2.5	A
$P_C$	Collector power dissipation	$T_C=25^\circ\text{C}$	80	W
$T_j$	Junction temperature		150	$^\circ\text{C}$
$T_{stg}$	Storage temperature		-55~150	$^\circ\text{C}$

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## CHARACTERISTICS

Tj=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEQ(SUS)}$	Collector-emitter sustaining voltage	$I_C=100mA$ ; $I_B=0$	800			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E=200mA$ , $I_C=0$	5			V
$V_{CEsat}$	Collector-emitter saturation voltage	$I_C=4A$ ; $I_B=0.8A$			5.0	V
$V_{BEsat}$	Base-emitter saturation voltage	$I_C=4A$ ; $I_B=0.8A$			1.5	V
$I_{CBO}$	Collector cut-off current	$V_{CB}=500V$ ; $I_E=0$			10	$\mu A$
$h_{FE}$	DC current gain	$I_C=1A$ ; $V_{CE}=5V$	8			
$V_F$	Diode forward voltage	$I_F=5A$			2.0	V

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Fig.2 Outline dimensions